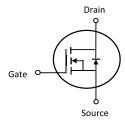
N Channel MOSFET

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Device Schematic

RoHS Compliant



Applications

- · Electronic Ballasts
- · LED Power Supply
- · High Efficiency Switch Mode Power Supplies

Features

- $R_{DS(ON)} = 0.5\Omega$ @ $V_{GS} = 10V$
- · High Switching Speed
- · Avalanche Energy Specified

Maximum Ratings @TA = +25°C

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	650	V	
Gate-Source Voltage	Vgss	±30		
Continuous Drain Current	lo	20	А	
Pulsed Drain Current (Note 2.)	Ірм	40		
Single Pulsed Avalanche Energy (Note 3.)	Eas	562	mJ	
Peak Diode Recovery dv/dt (Note 4.)	dv/dt	2.46	V/ns	
Power Dissipation	PD	65	W	
Junction Temperature	Tj	150	°C	
Storage Temperature Range	Тѕтс	-55 to +150		

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating : Pulse width limited by maximum junction temperature.
- 3. L = 10mH, I_{AS} = 10.5A, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25 $^{\circ}$ C
- 4. IsD ≤ 20A, di/dt ≤ 200A/µs, VDD ≤ BVDSS, Starting TJ = 25°C

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N Channel MOSFET



Electrical Characteristics @TA = +25°C

Parameter	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
OFF Characteristics						•
Drain-Source Breakdown Voltage	Vgs=0V, Id=250µA	VDSS	650			V
Gate-Source Leakage Current	V _{DS} =0V, V _{GS} =30V	Igss	ĺ	100		
Gate-Source Leakage Current	V _{DS} =0V, V _{GS} =-30V				-100	nA
Drain-Source Leakage Current	V _{DS} =650V, V _{GS} =0V	IDSS			10	μA
ON Characteristics						
Gate-Threshold Voltage	Vos=Vgs, Io=250µA	V _{th(GS)}	2		4	V
Static Drain-Source On-State Resistance	Vgs=10V, ID= 10A	Rds(on)			0.5	Ω
Dynamic Characteristics						
Input Capacitance	V _{DS} =25V, V _{GS} =0V, F=1MHz	Cıss	-	2512		pF
Output Capacitance		Coss	-	231		
Reverse Transfer Capacitance		Crss	-	14		
Switching Characteristics						•
Turn-On Delay Time	V _{DD} =100V, V _{GS} =10V, I _D =20A,R _G =25Ω(Note 1,2)	td(on)		28		
Turn-On Rise Time		tr] - -	35		
Turn-Off Delay Time		t _{D(OFF)}		140		ns
Turn-Off Fall Time		tr		76		
Switching Characteristics						
Total Gate Charge (Note 1)	V _{DS} =100V, V _{GS} =10V, I _D =20A,I _G =1mA(Note 1,2)	Q G		54		nC
Gate-Source Charge		Qgs		10		
Gate-Drain Charge		Q _{GD}		13		
Drain-Source Diode Characteristics And Ma	ximum Ratings					
Drain-Source Diode Forward Voltage(Note 1)	Is=20A, Vgs=0V	VsD			1.4	V
Maximum Body-Diode Continuous Current		ls	-		20	Α
Maximum Body-Diode Pulsed Current		Іѕм			40	
Reverse Recovery Time(Note 1)	V _{GS} =0V, I _S =20A, dI _F /dt=-100A/µs (Note 1)	trr		506		ns
Reverse Recovery Charge		Qrr		9		μC
Notes:1. Pulse Test:Pulse Width ≤300us,Duty 0 2. Essentially independent of operating to	•				_	

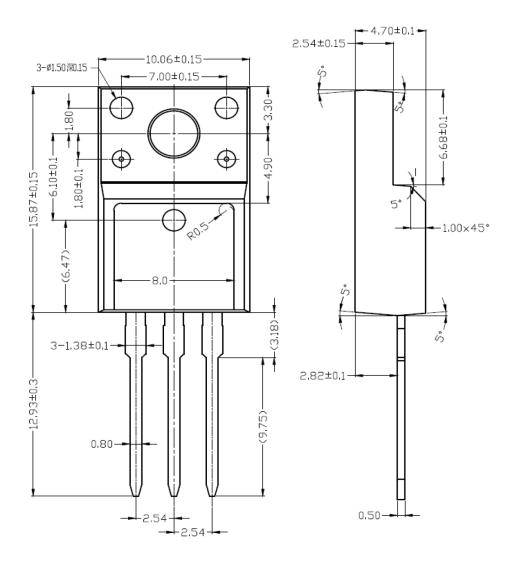
Dimensions: Millimetres



N Channel MOSFET



Outline Dimensions



Part Number Table

Description	Part Number		
N Channel MOSFET, 650V, 20A, TO-220F	HMF20N65S		

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